

EAST - [10650000.wsp:1]

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L1: (1) ("3502951").PN.
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 L3: (1) ("4937647").PN.
 L4: (1) ("5156969").PN.
 L5: (1) ("5485027").PN.
 L6: (1:106) controlled near rectifier
 L7: (105) controlled near rectifier and silicon and substrate and epitaxial and polysilicon

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 controlled near rectifier and silicon and substrate and epitaxial and polysilicon

	u	i	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20050006706 A1	20050113	13	Symmetrical high frequency SCR structure and method	257/368	438/133
2	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20040233255 A1	20041125		INKJET PRINTER HAVING IMPROVED EJECTOR CHIP	347/63	
3	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20040217425 A1	20041104		Efficient protection structure for reverse pin-to-pin electrostatic discharge	257/360	
4	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20040119087 A1	20040624		Breakdown voltage for power devices	257/100	257/E29.013; 257/E29.198; 257/E29.211; 257/107;
5	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20040067609 A1	20040408		Silicon controlled rectifier for sige process, manufacturing method thereof and integrated circuit including the same	438/133	257/E29.211
6	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20040051147 A1	20040318		Method for making high-gain vertical bipolar junction transistor structures compatible with CMOS process	257/368	257/370; 257/E21.375;
7	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20040033645 A1	20040219		Novel silicon-controlled rectifier structures on silicon-on insulator with shallow trench isolation	438/133	257/E21.696; 257/E21.564; 257/E21.703;
8	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20040027745 A1	20040212		Drain-extended MOS ESD protection structure	361/56	257/E21.112

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